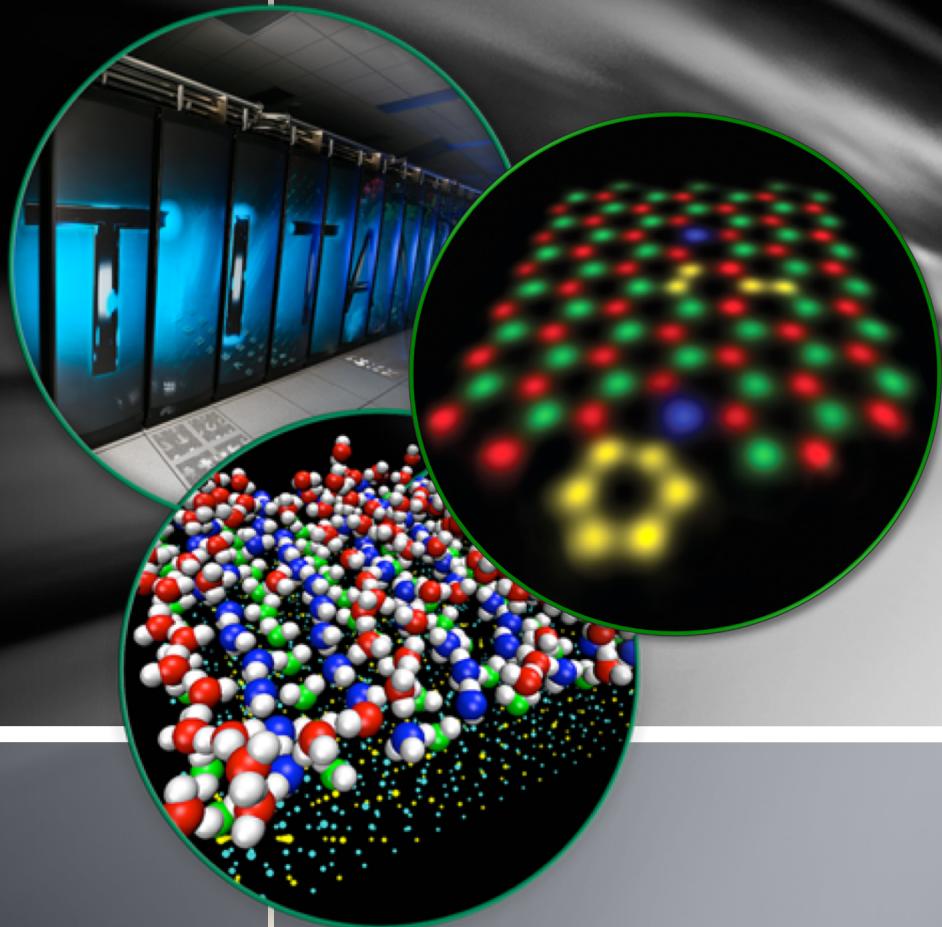


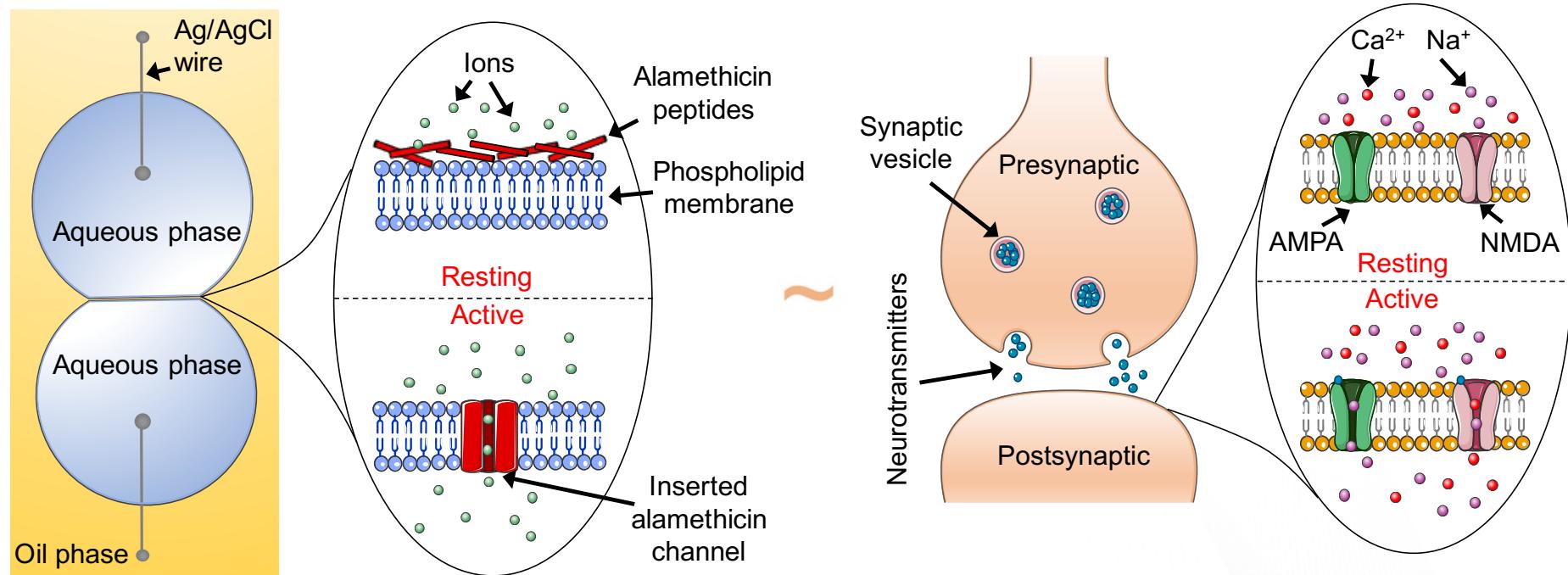
Two-terminal, soft, biomembrane-based devices that can sense, process, and learn



Joseph Najem
Andy Sarles
Pat Collier
Alex Belianinov
Katie Schuman

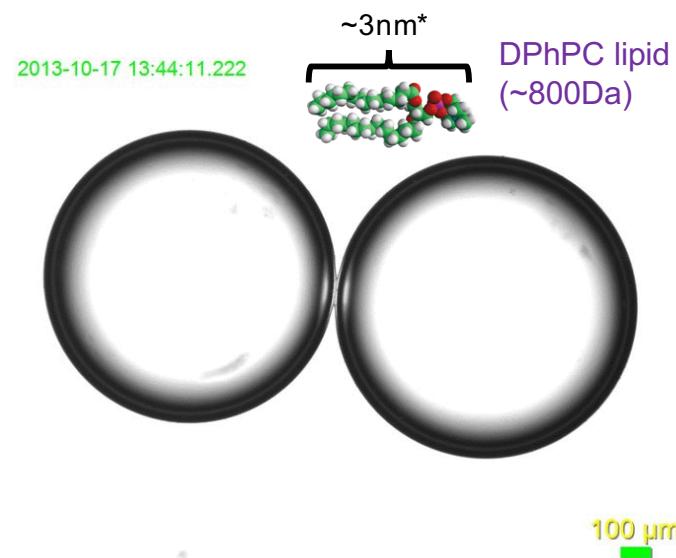
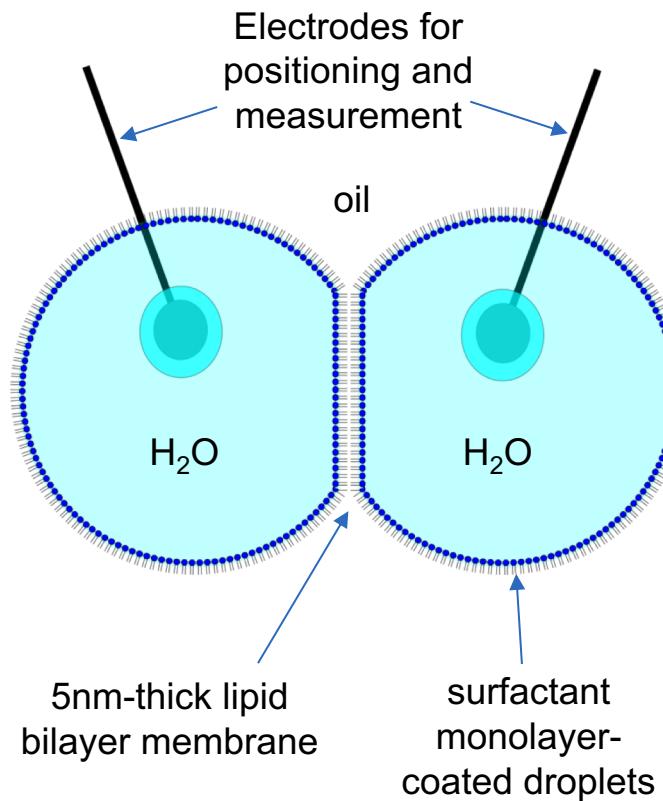


Concept for a two-terminal biomolecular memristor featuring similar structure (biomembrane), switching mechanism (ion channels), and ionic transport modality as biological synapses while operating at considerably lower power.



- Biological synapses enable electrochemical transport of information. Key processes are voltage and ion-selective transport via transmembrane channels.
- The behaviors of synthetic memristors are largely phenomenological; they are also noisy and power-hungry!

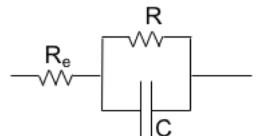
Droplet Interface Bilayers: insulating model membranes



Funakoshi, K., H. Suzuki, and S. Takeuchi, Anal. Chem., 2006. 78(24): p. 8169-8174.
Holden, M.A., et al., J. Am. Chem. Soc., 2007. 129(27): p. 8650-8655.
Hwang, W.L., et al., J. Am. Chem. Soc., 2008. 130(18): p. 5878-5879.
Poulin, P.; Bibette, J., Langmuir 1998, 14 (22), 6341-6343.

Building blocks for cell-inspired compartmentalized materials...

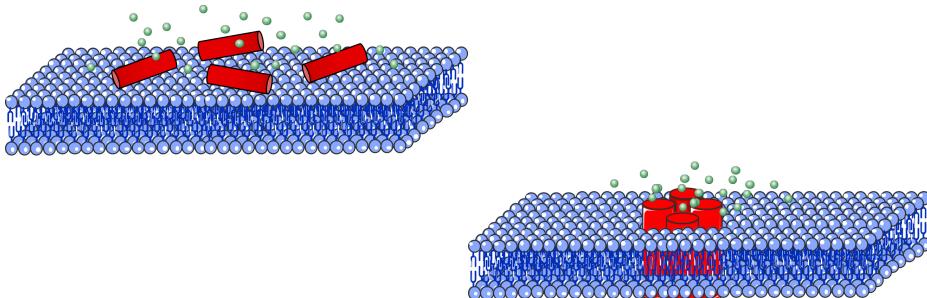
Equivalent circuit



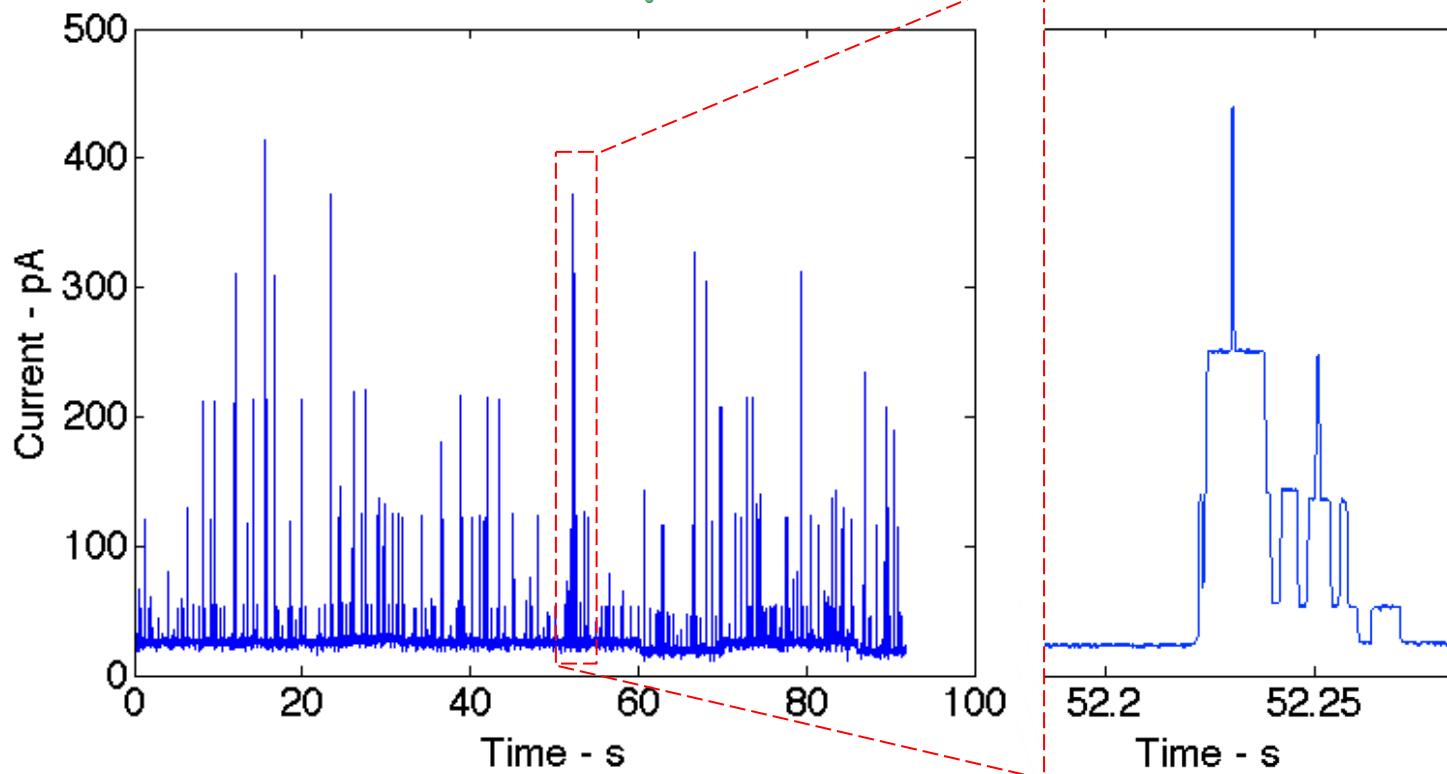
$$R_m \equiv R \times A$$

$$C_m \equiv \frac{C}{A} = \frac{\epsilon}{d}$$

Alamethicin peptides form voltage-dependent ion channels

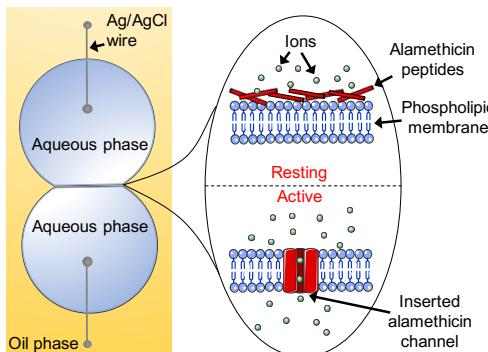
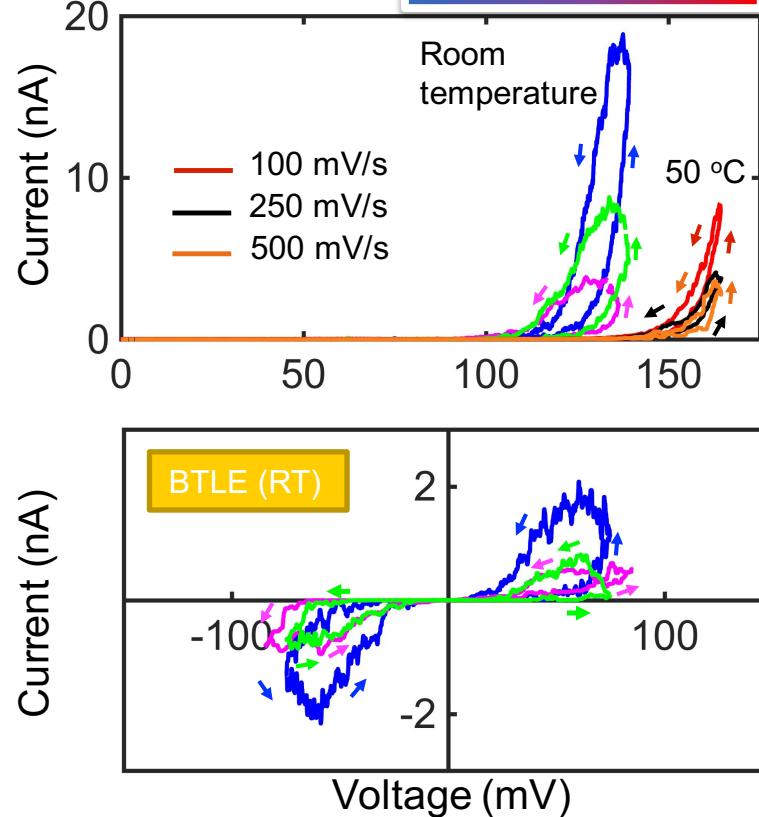
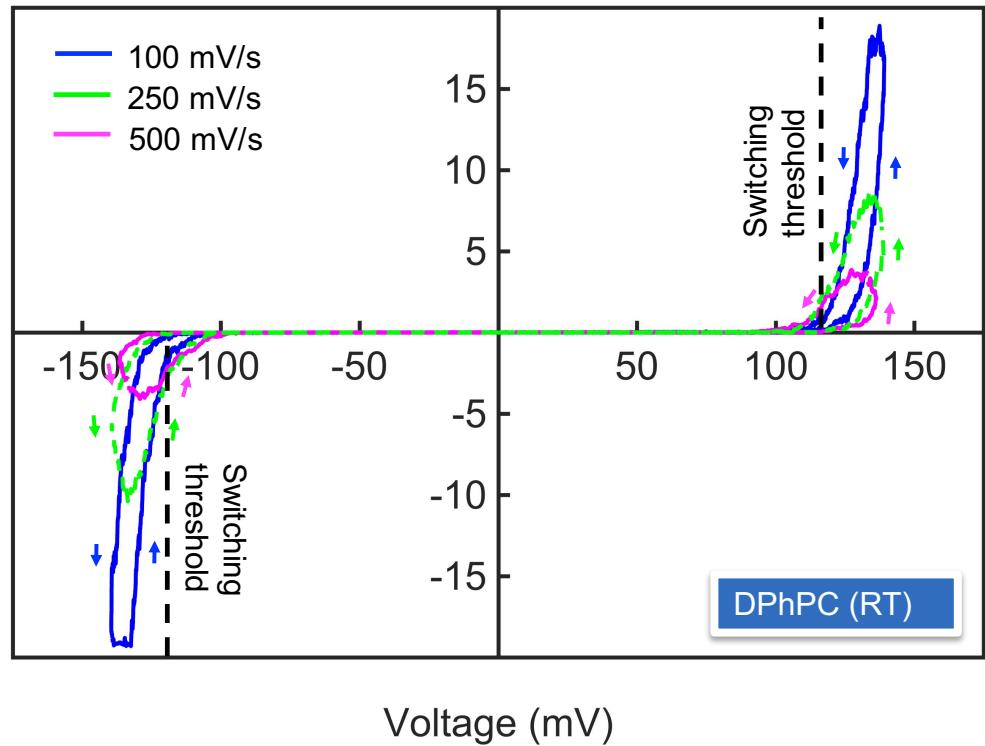


Conductive pathways are created in the insulating membrane in response to voltage



Current-voltage relationships of alm-doped biomembranes

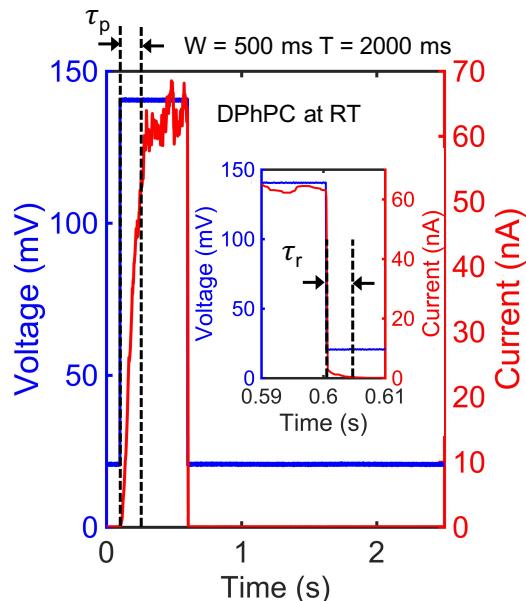
Current (nA)



“...a memristor is best defined as any two-terminal device that exhibits a pinched hysteresis loop in the voltage–current plane when driven by any periodic voltage...”

Chua, L., *Semiconductor Science and Technology* 2014, 29 (10), 104001.

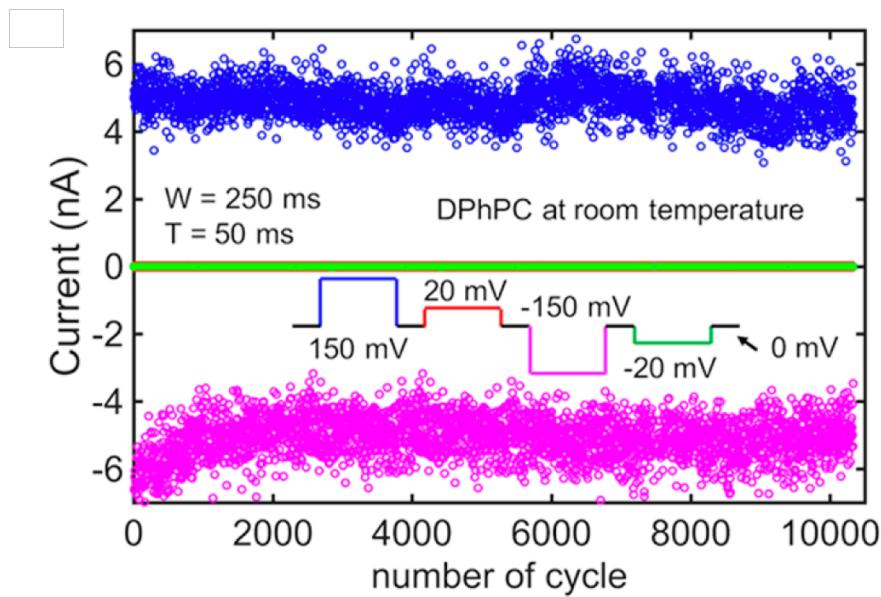
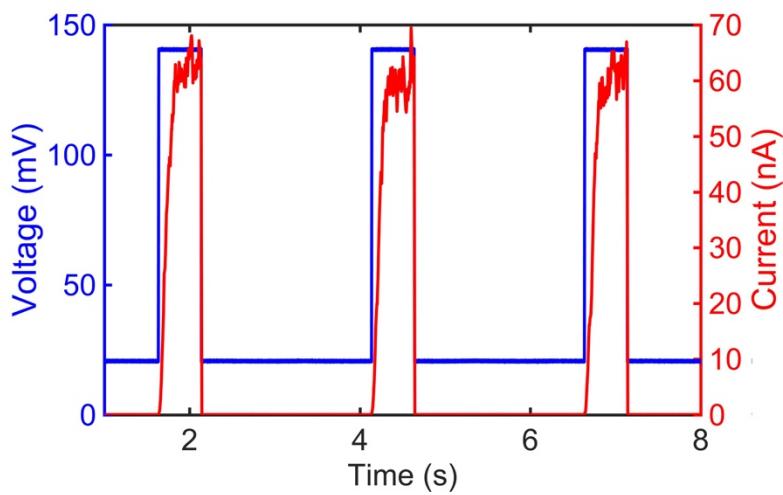
Dynamic switching performance and switching longevity



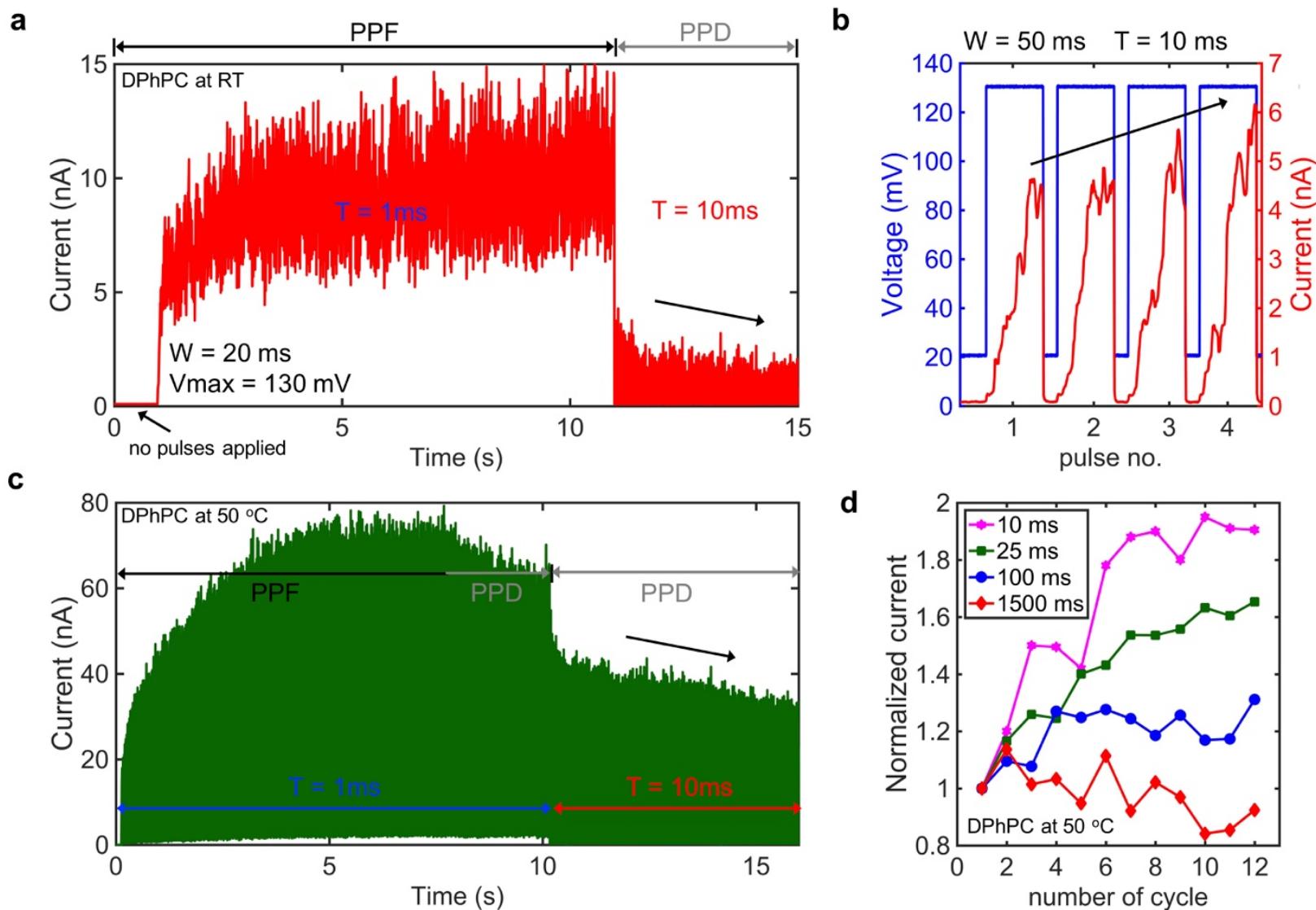
Lipid type	Temperature	$V_{\text{threshold}}$ (mV)	τ_r (ms)	τ_p (ms)	τ_d (ms)
DPhPC	RT	120	6.8 ± 1.2	99.5 ± 17.7	1 ± 1.3
DPhPC	50°C	150	3.7 ± 0.5	75.1 ± 11.1	8.55 ± 2.74
BTLE	RT	25	100 ± 37	420 ± 61.2	23.3 ± 6.11

NMDA relaxation ~ 100 's of ms

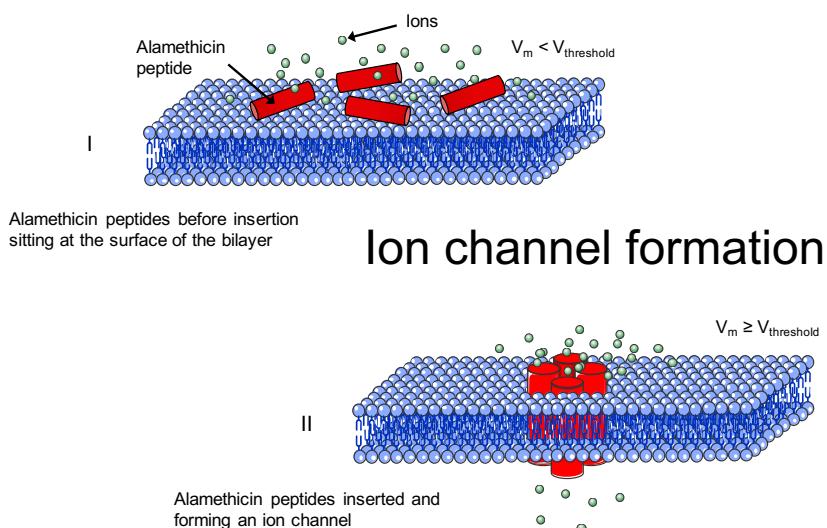
Lester, R. A. J., et al., *Nature* 1990, 346, 565.



Short-term learning across multiple voltage pulses (PPF & PPD)

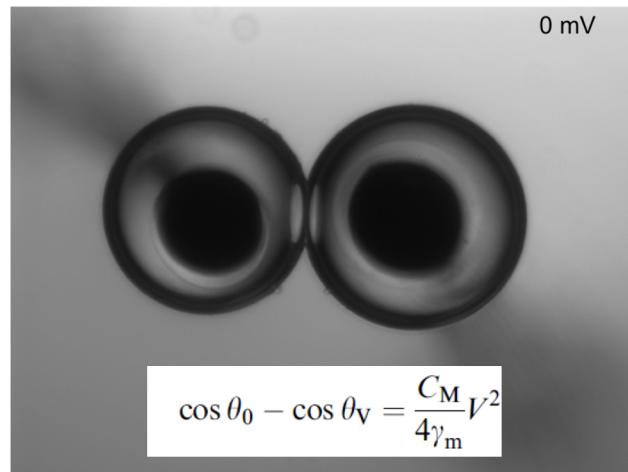


So, what “states” are dictating these responses?



Ion channel formation

Electrowetting



$$I = G(N_a, A_m)V$$

N_a = number of alm pores per m^2

A_m = fractional change in area due to EW

$$\frac{dN_a}{dt} = \frac{1}{\tau_0 e^{V/V_e}} (N_0 e^{V/V_e} - N_a)$$

Dynamics of alamethicin gating

Okazaki, T., et al., Biophysical Journal 2003, 85 (1), 267-273.

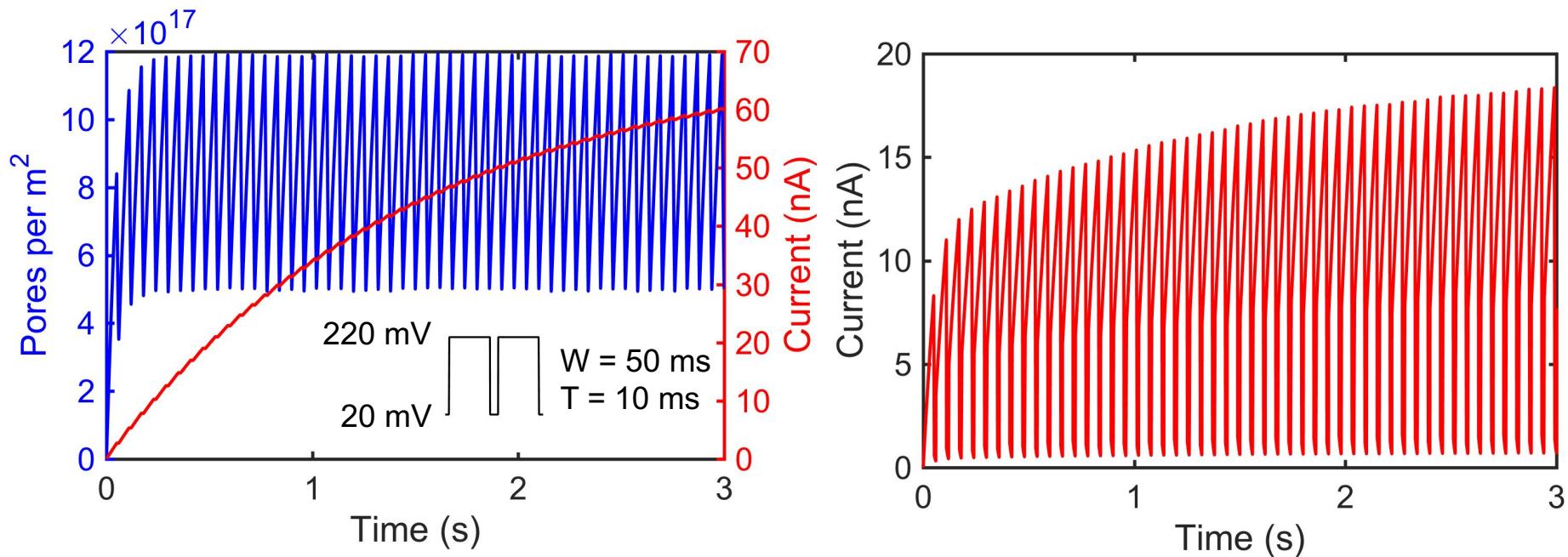
$$\frac{dA_m}{dt} = \frac{1}{\tau_{ew}} (\alpha v^2 - A_m(t))$$

Dynamics of electrowetting

$$G(V, t) = G_u N_a(V, t) A_0 (1 + A_m(t))$$

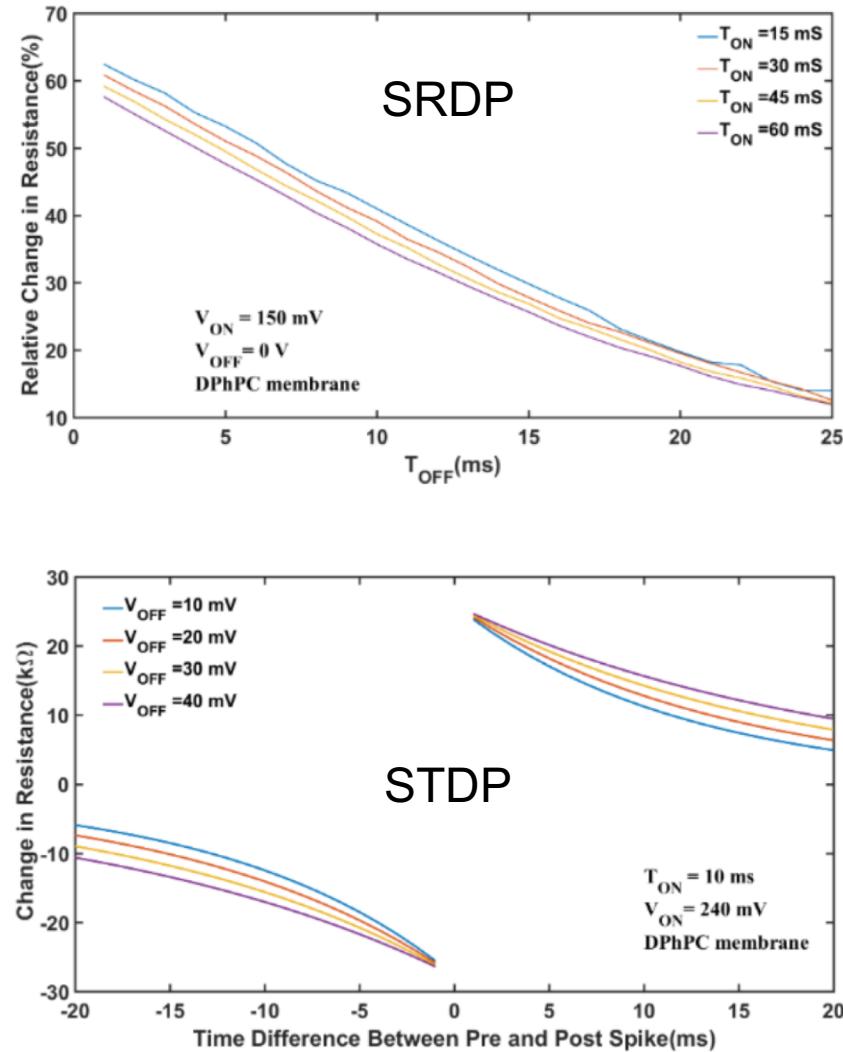
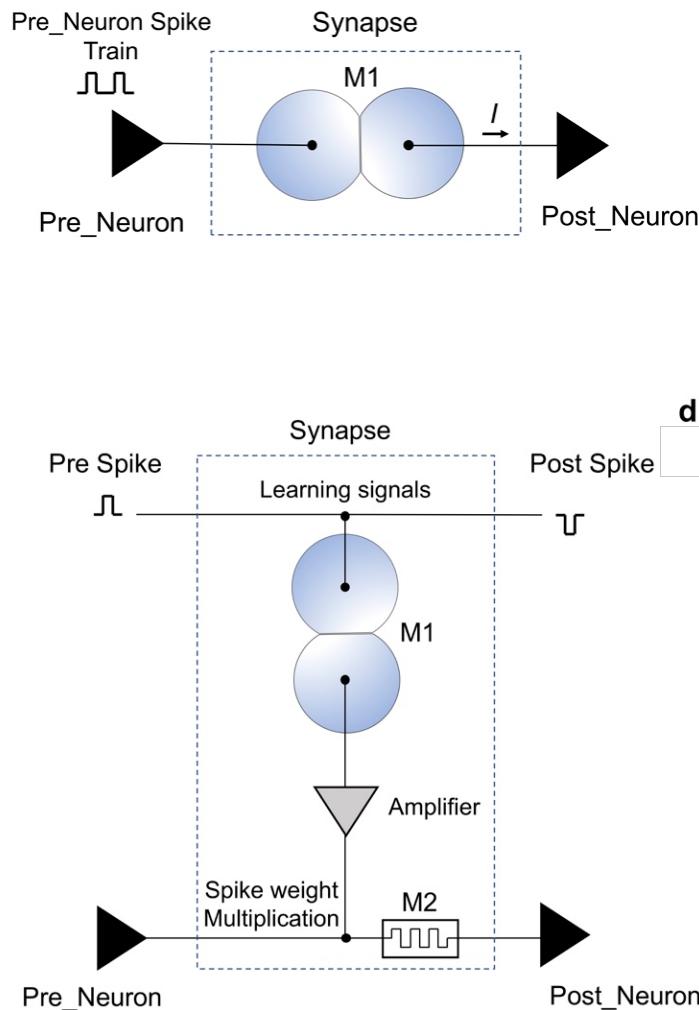
Reciprocal of memristance

Simulations of short-term plasticity in a biomolecular memristor



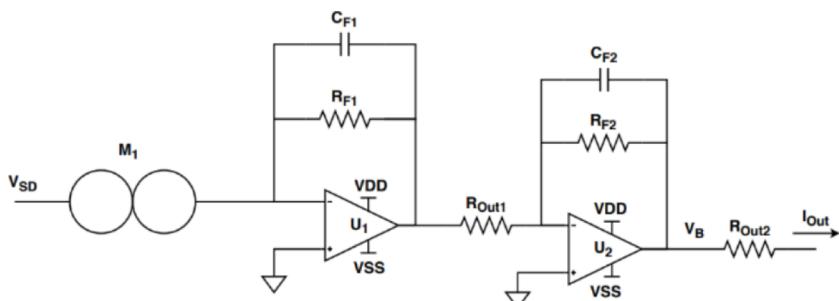
Slow formation of new bilayer area and fast insertion of new channels leads to PPF-like short-term learning responses!

Online learning circuit application: Short- and Long-term learning

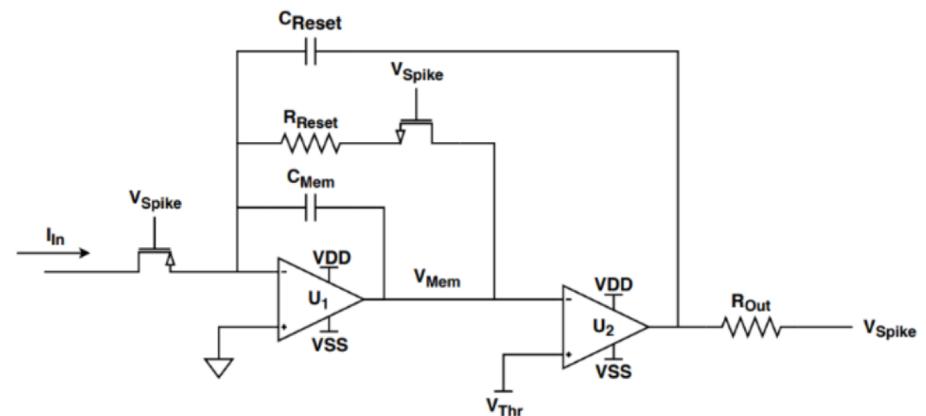


Experimental demonstration of short-term learning

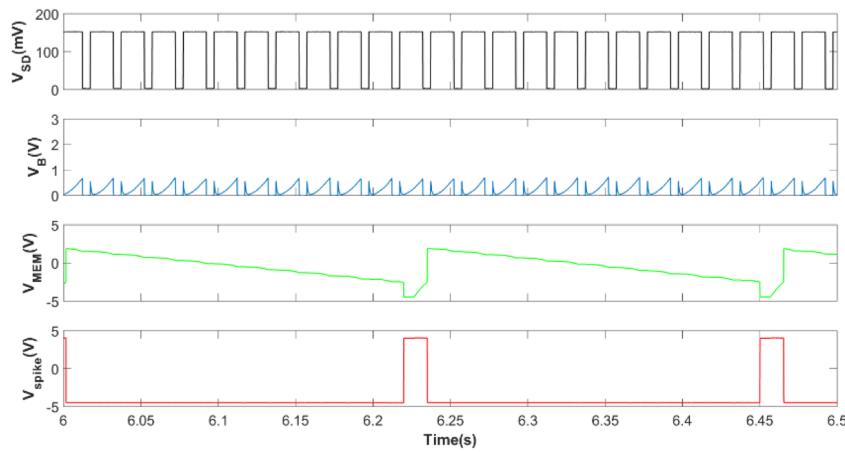
Synapse



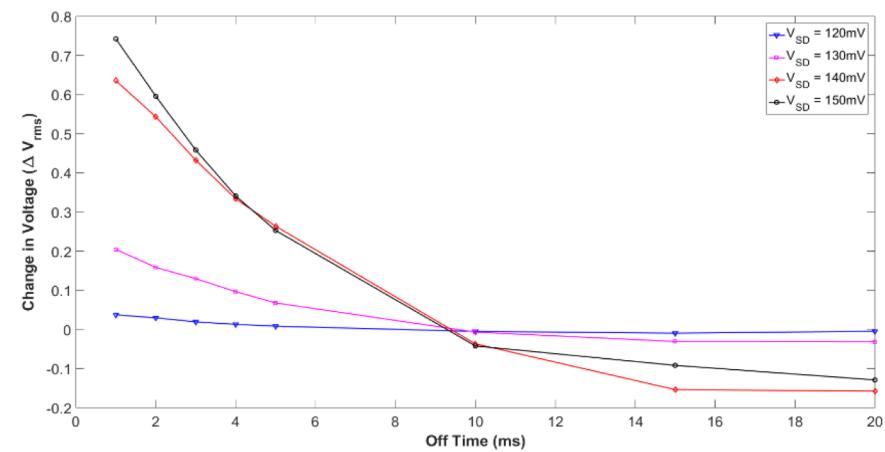
Neuron



Spike trains test voltages for 5ms off time

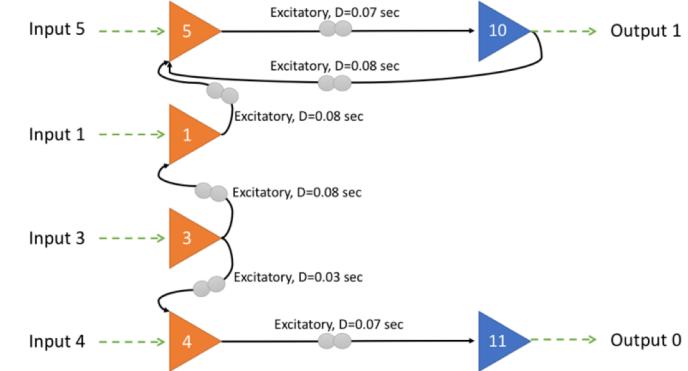
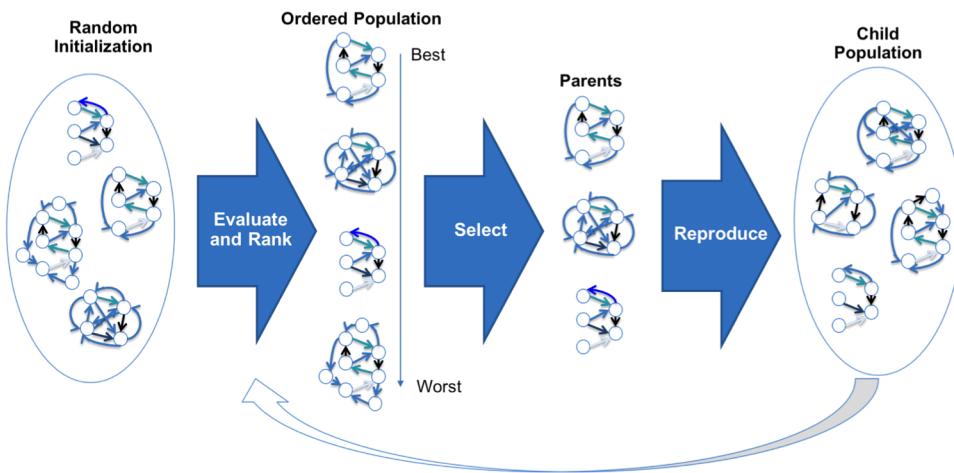


Spike-rate-dependent Plasticity



How do we train DIB-based neuromorphic systems?

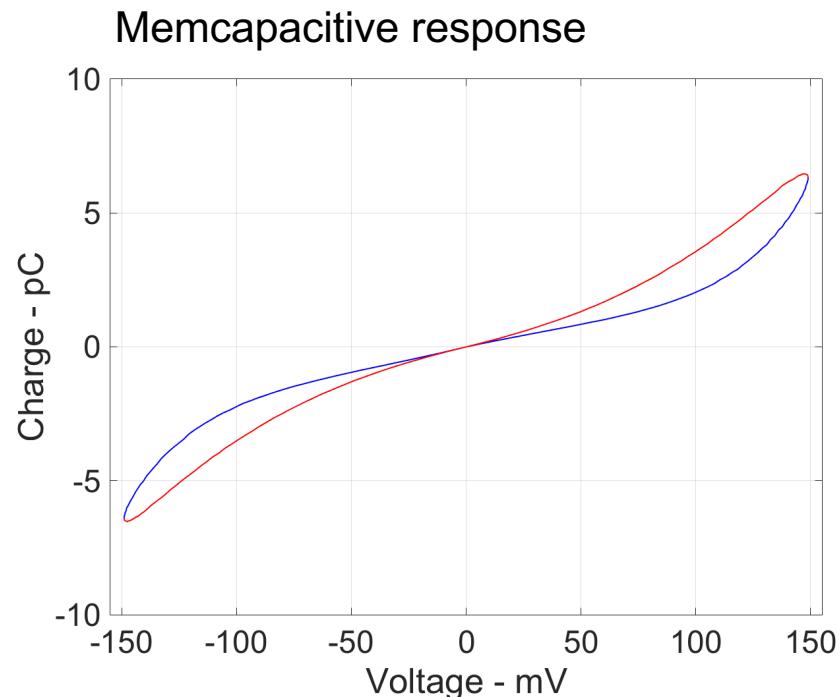
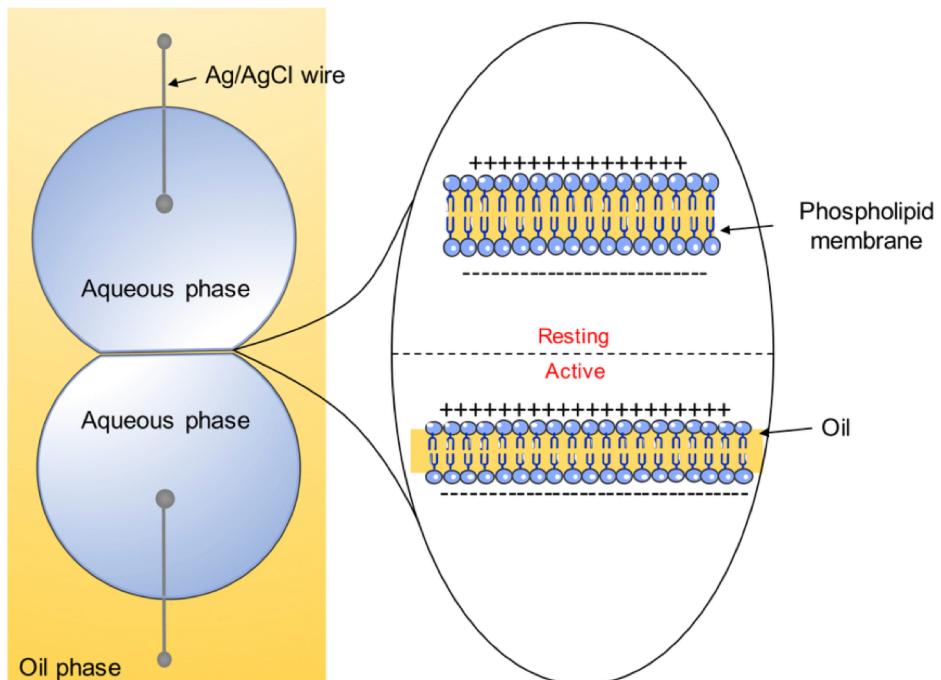
Evolutionary Optimization for Neuromorphic Systems (EONS)



Network for EEG classification task:
Training Accuracy: 98.5%
Testing Accuracy: 98.5%
6 neurons, 6 synapses

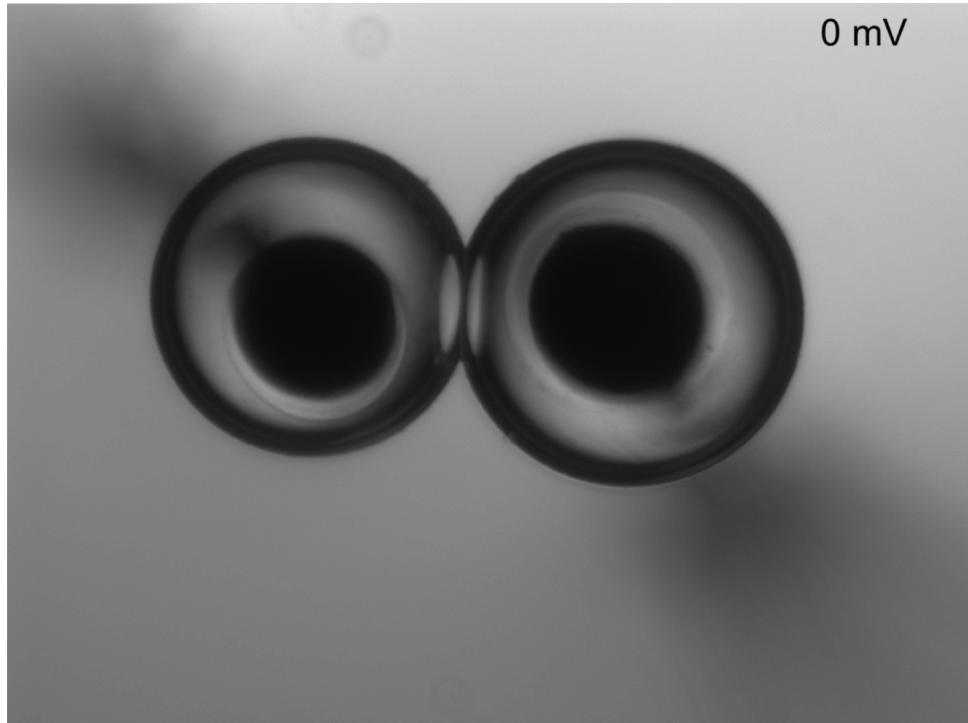
Reconfigurable soft-matter interfaces exhibit memory capacitance too!

The same setup void of any memristive ion channels exhibits a memcapacitive behavior. Memcapacitors have been theorized but never realized.



The geometry of the bilayer interface changes in response to voltage

The same setup void of any memristive ion channels exhibits a memcapacitive behavior. Memcapacitors have been theorized but never realized.



Upon application of a transmembrane voltage bias v (DC or AC) two phenomena occur:

- 1) **Electrowetting** which results in an increase in membrane area (i.e. radius r) driven by changes in surface tension.
- 2) **Electrocompression** which results in a decrease in membrane thickness (w) driven by compressive forces generated by the attraction between opposite charges.

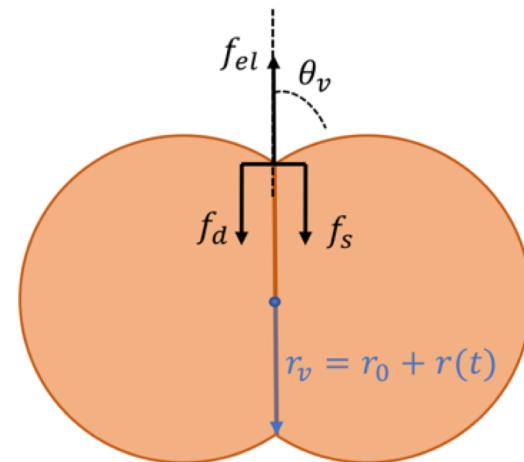
State variable and equations

$$\mathbf{q} = \mathbf{C}(r, w)\mathbf{v}$$

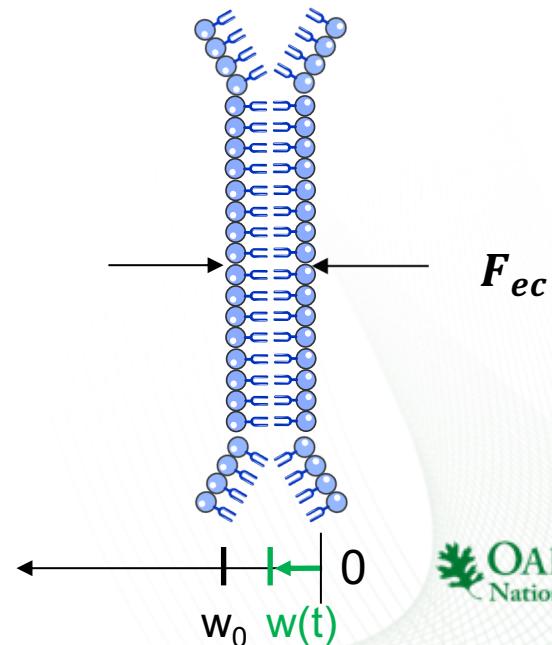
$$\xi_{ew} \frac{dr(t)}{dt} + k_{ew} r(t) = f_{el}(t)$$

$$\xi_{ec} \frac{dw(t)}{dt} + k_{ec} w(t) = F_{ec}(t)$$

$$V = v(t)$$

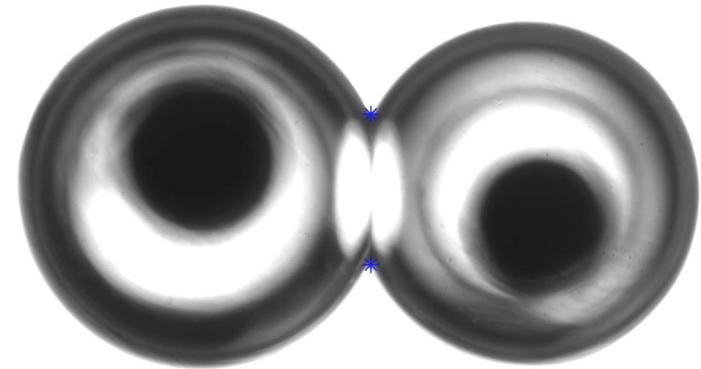
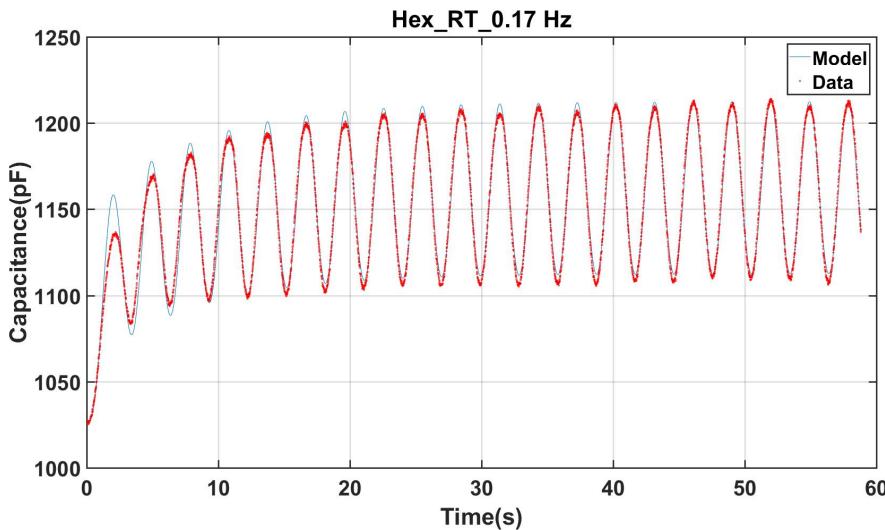


$$f_{el} = f_d + f_s$$



State variable and equations

Hexadecane
Sinusoidal (150 mV, 0.17Hz)



$$\frac{dR_1}{dt} = R_2$$

Electrowetting

$$\frac{dR_2}{dt} = \frac{-R_2^2}{R_1} + \frac{k_{ew}r_0R_2}{\xi_{ew}R_1} - \frac{2k_{ew}R_2}{\xi_{ew}} + \frac{\varepsilon\varepsilon_0\nu^2R_2}{\xi_{ew}R_1W_1} - \frac{\varepsilon\varepsilon_0\nu^2W_2}{\xi_{ew}W_1^2} + \frac{\varepsilon\varepsilon_0\nu\dot{\nu}}{\xi_{ew}W_1}$$

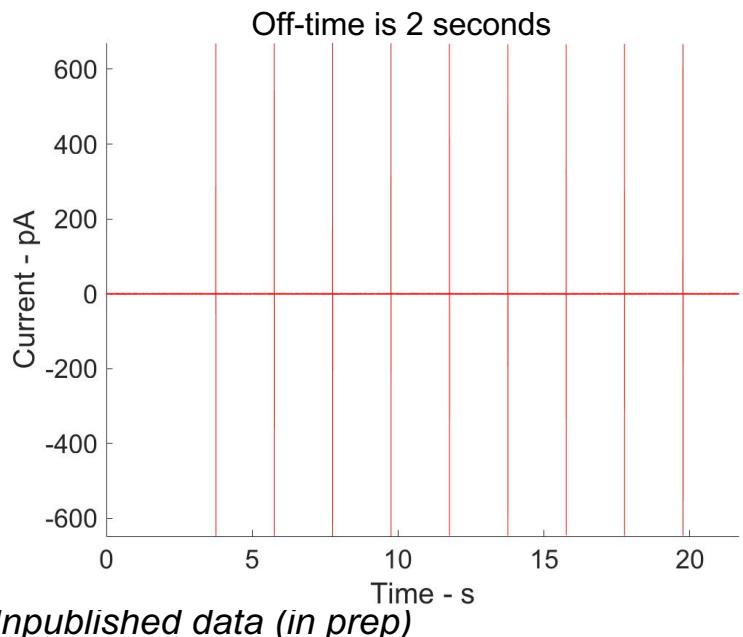
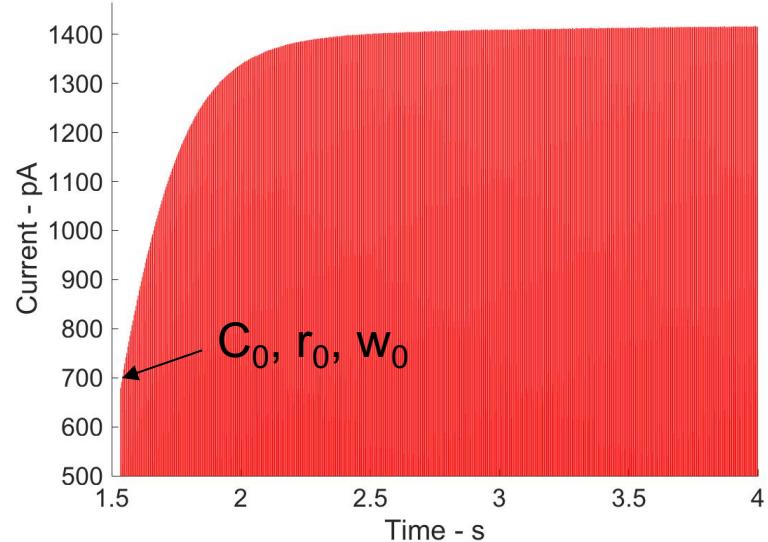
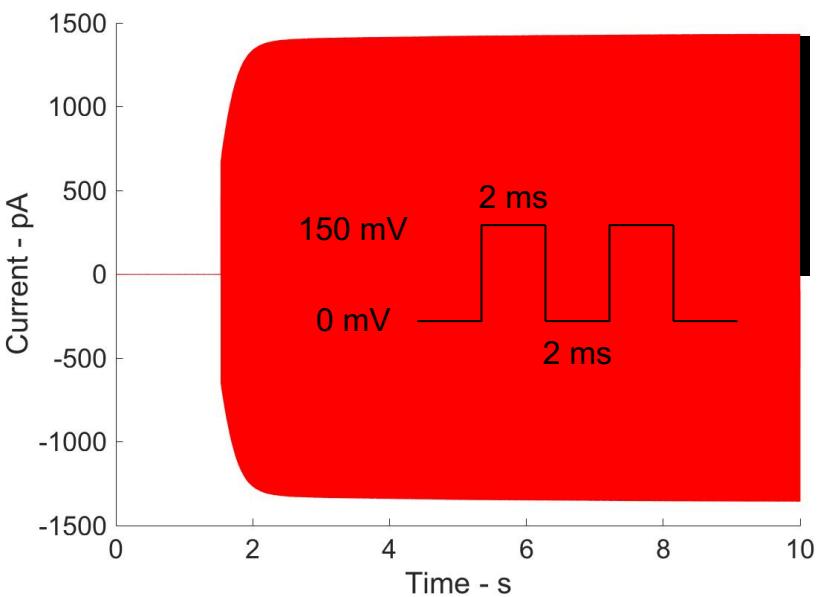
$$\frac{dW_1}{dt} = W_2$$

Electrocompression

$$\frac{dW_2}{dt} = \frac{-W_2(k_{ec}W_1^3 + \beta\nu^2R_1^2)}{\xi_{ec}W_1^3} + \frac{\beta\nu(\nu R_1 R_2 + 0.5R_1^2\dot{\nu})}{\xi_{ec}W_1^2}$$

- The units for ξ_{ew}, k_{ew} are **(N.s/m²)** and **(N/m²)**, respectively
- The units for ξ_{ec} and k_{ec} are **(N.s/m)** and **(N/m)**, respectively

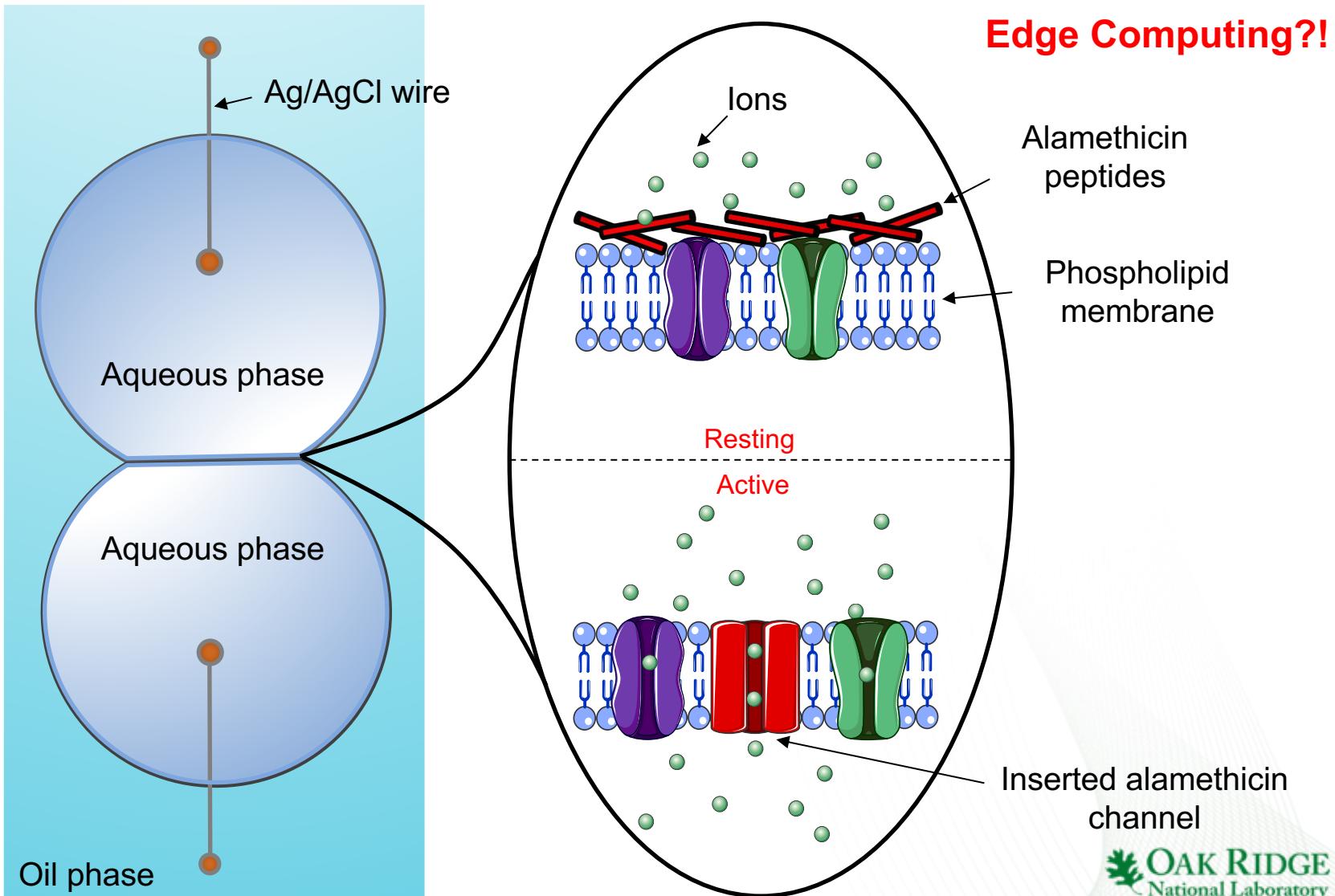
Plasticity and signal processing



There are two time constants, one related to EC (the quick rise) and the other related to EW (the slow rise)...

Our system is great for sensing and signal processing applications

We are not limited to a single type of ion channels. Multiple stimuli-responsive ion channels could be used for applications in sensing and signal processing.



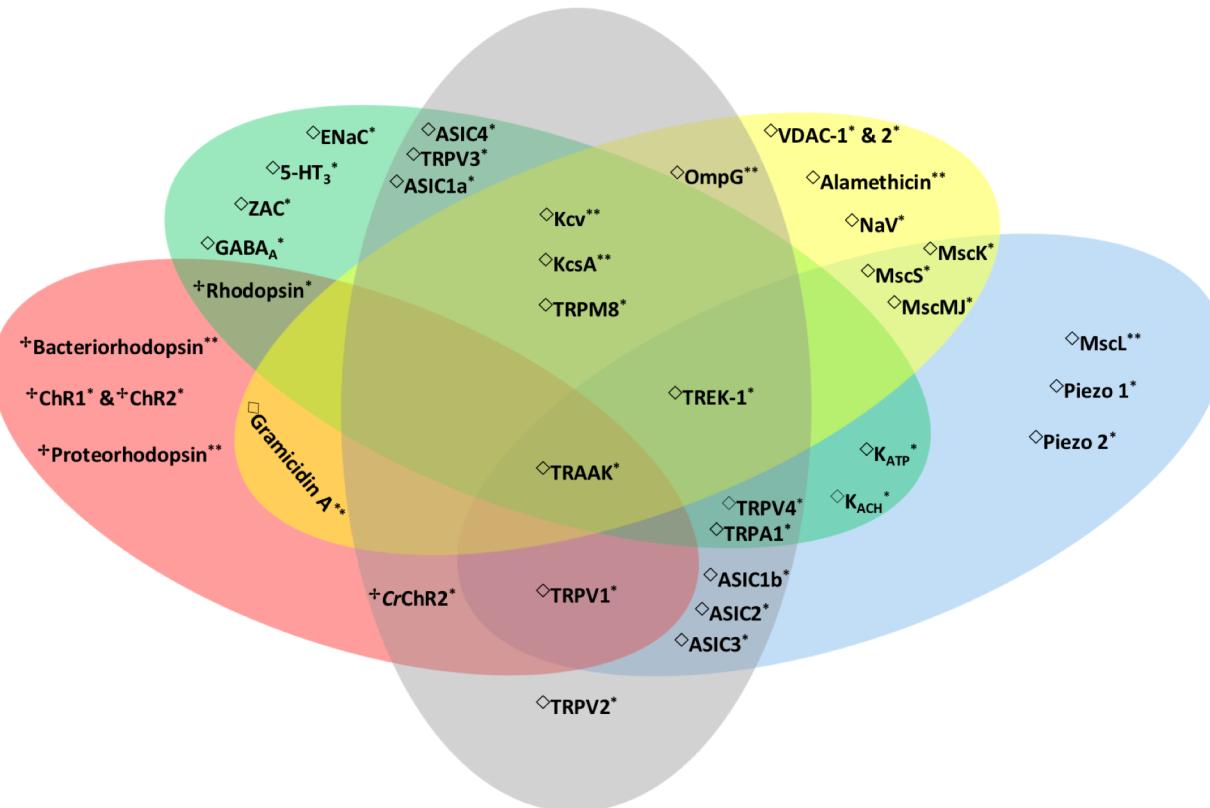
A wide variety of ion channels and pumps could be investigated

*Reconstituted

**Reconstituted in DIBs

◇ Ion channel

⊕ Ion pump



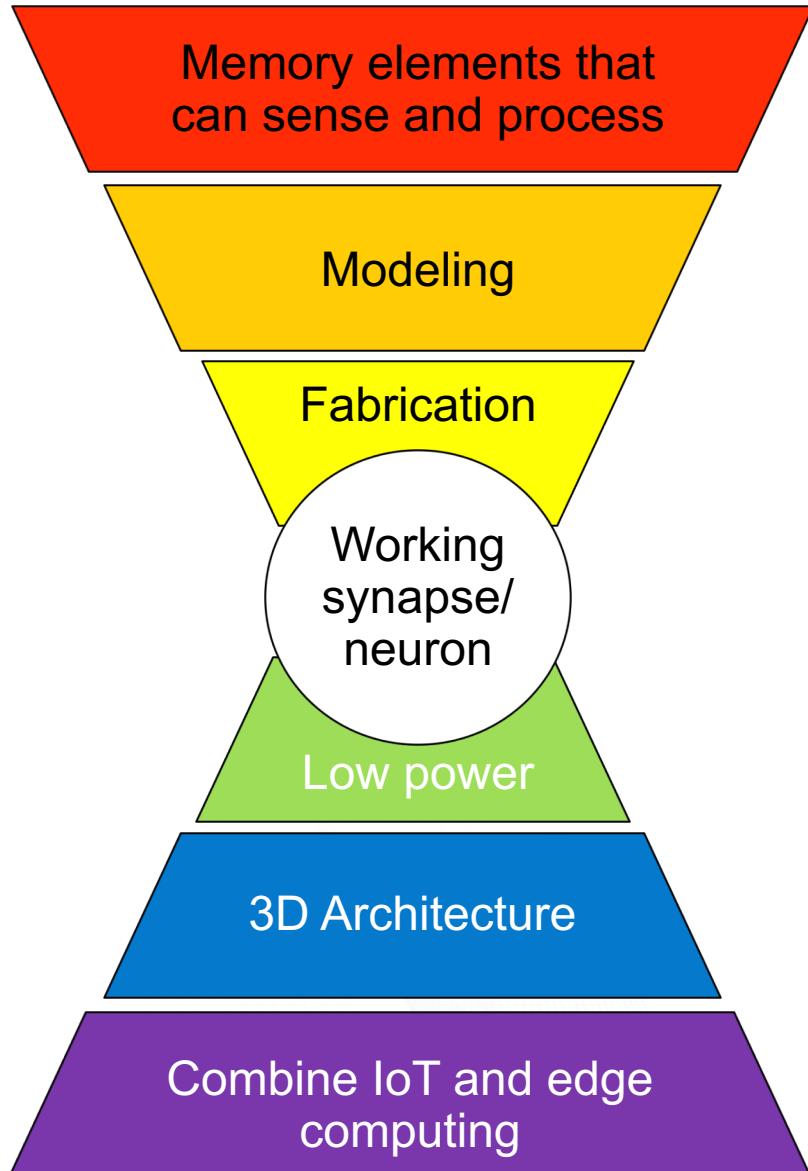
Light-gated Voltage-gated Tension-gated Ligand/Chemical-gated Temperature/pH-gated

We would like to thank:

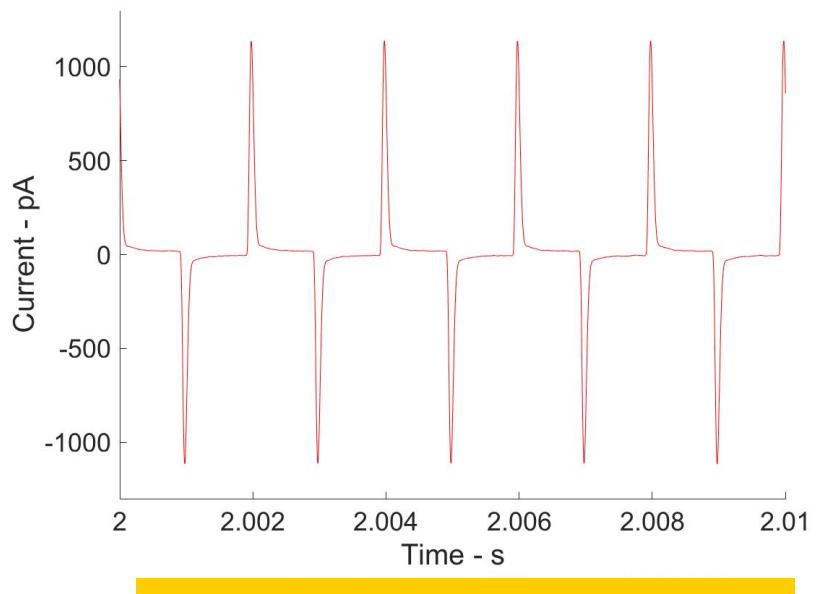
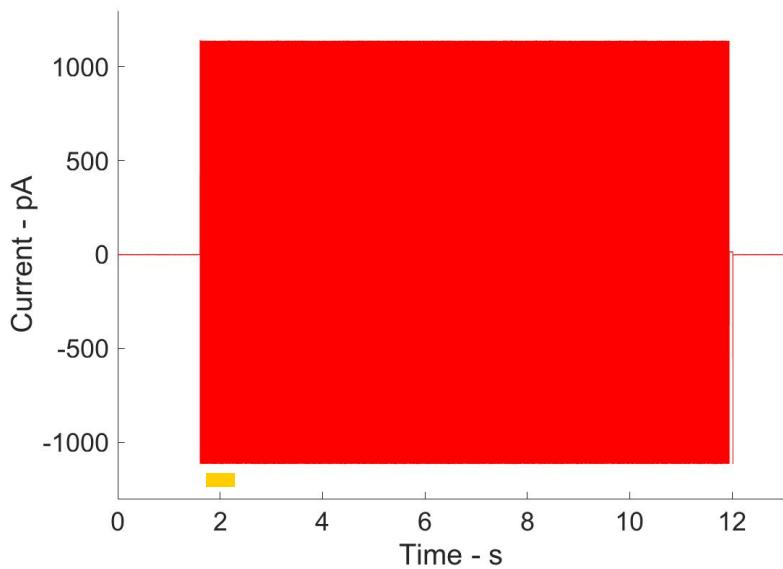
- Oak Ridge National Laboratory for funding this work
- Oak Ridge Leadership Computing Facility for providing computing support
- The National Science Foundation for funding this work
- Dr. R. Stanley Williams for his valuable input, suggestions, and insights

If you have any questions or suggestions please send me an email at
najemjs@ornl.gov

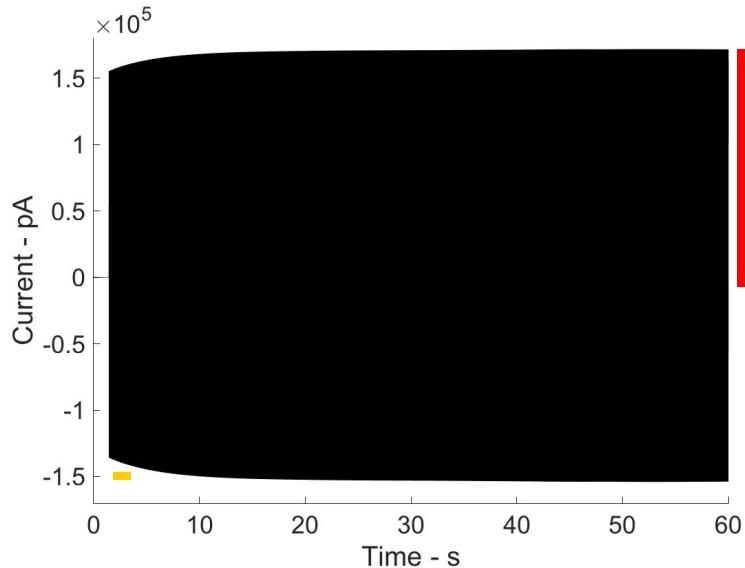
- Oak Ridge National Lab is a national leader in computation and materials research
- We are approaching the end of **Moore's law** era.
- The reliability of the IoT, edge, and cloud computing is **exponentially growing**.
- **Power consumption and environmental considerations** are the main problems humanity faces this century
- **Crosscutting efforts** in chemistry, biology, engineering and computation (with all the right people and ingredients available locally)
- Insight into the evolutionary path of many species



Response to pulses – control



Response to pulses – Hexadecane at RT



Pulse amplitude = 150 mV

Pulse width = 2ms

Off-time= 2ms

